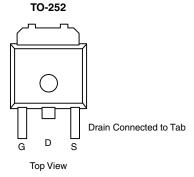




P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 60	0.015 at V _{GS} = - 10 V	- 50 ^d			
- 60	0.020 at V _{GS} = - 4.5 V	- 50 ^d			



Ordering Information

SUD50P06-15-GE3 (Lead (Pb)-free and Halogen-free) SUD50P06-15-T4-GE3 (Lead (Pb)-free and Halogen-free)

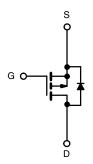
FEATURES

- TrenchFET® Power MOSFET
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

· Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V_{DS}	- 60	V			
Gate-Source Voltage	V _{GS}	± 20	7			
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	I_	- 50 ^d			
Continuous Diam Guiterit (1) = 173 C)	T _C = 125 °C	I _D	- 27.5			
Pulsed Drain Current	I _{DM}	- 80	A A			
Avalanche Current		I _{AS}			- 50	
Single Pulse Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ		
Power Dissination	T _C = 25 °C	P _D	113 ^c	w		
Power Dissipation	T _A = 25 °C	' D	2.5 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Junction-to-Ambient ^b	t ≤ 10 s	- R _{thJA}	15	18	°C/W		
Junction-to-Ambient*	Steady State		40	50			
Junction-to-Case		R _{thJC}	0.82	1.1			

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.

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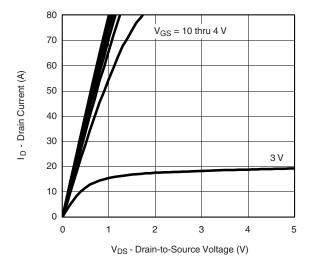
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA - 60				V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$ $V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 \text{ °C}$			- 50	μΑ	
					- 100		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 50			Α	
		V _{GS} = - 10 V, I _D = - 17 A	0.01		0.015		
	В	$V_{GS} = -10 \text{ V}, I_D = -50 \text{ A}, T_J = 125 ^{\circ}\text{C}$			0.025		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 50 A, T _J = 150 °C			0.028		
		V _{GS} = - 4.5 V, I _D = - 14 A			0.020		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		61		S	
Dynamic ^b	*			•			
Input Capacitance	C _{iss}			4950			
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		480		pF	
Reverse Transfer Capacitance	C _{rss}]		405			
Total Gate Charge ^c	Qg			110	165		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -50 \text{ A}$		19		nC	
Gate-Drain Charge ^c	Q_{gd}]		28			
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 0.6 Ω		70	105		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -50 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6 \Omega$		175	260	ns	
Fall Time ^c	t _f]		175	260		
Source-Drain Diode Ratings and Cha	racteristics	T _C = 25 °C ^b					
Continuous Current	Is				- 50	^	
Pulsed Current	I _{SM}				- 80	Α	
Forward Voltage ^a	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		- 1	- 1.6	V	
Reverse Recovery Time	t _{rr}	I _F = - 50 A, dI/dt = 100 A/μs		45	70	ns	

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

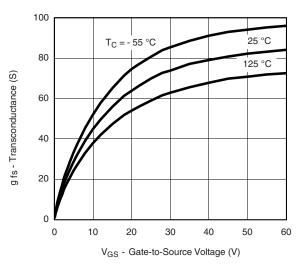
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



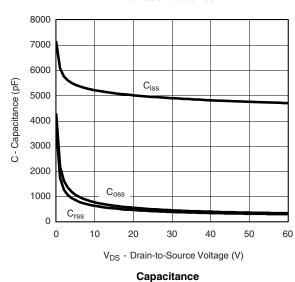
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



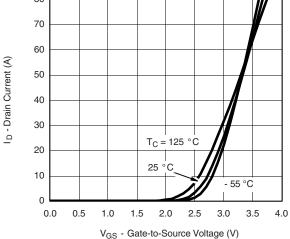
Output Characteristics



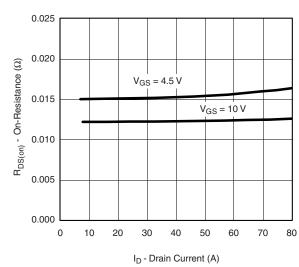
Transconductance



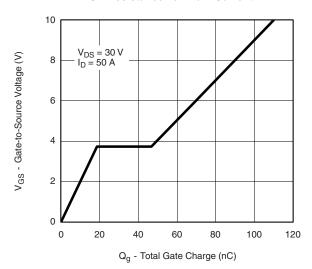
80



Transfer Characteristics



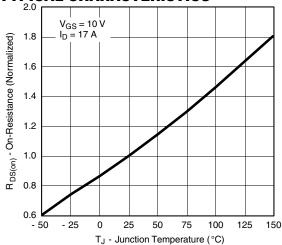
On-Resistance vs. Drain Current



Gate Charge

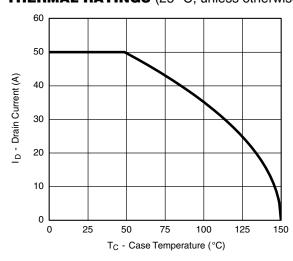
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TYPICAL CHARACTERISTICS

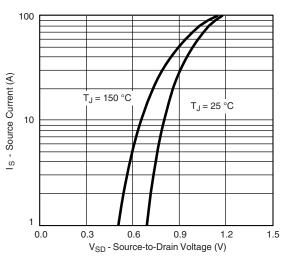


On-Resistance vs. Junction Temperature

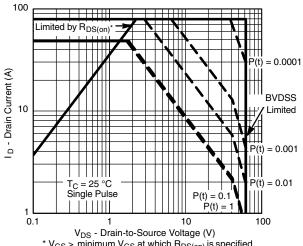
THERMAL RATINGS (25 °C, unless otherwise noted)



Drain Current vs. Case Temperature

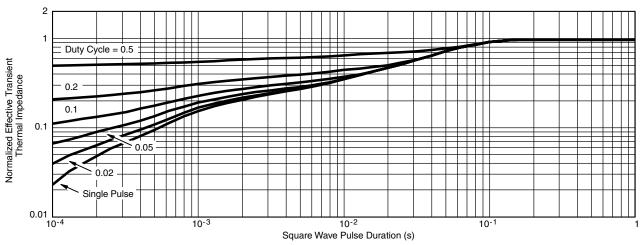


Source-Drain Diode Forward Voltage



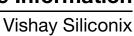
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

Safe Operating Area



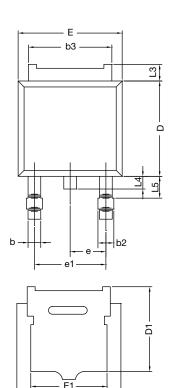
Normalized Thermal Transient Impedance, Junction-to-Case

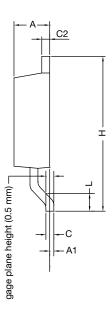
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68940.





TO-252AA Case Outline





	MILLIMETERS		INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	4.10	-	0.161	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28 BSC		0.090 BSC			
e1	4.56	BSC	0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.01	1.52	0.040	0.060		
ECN: T16-0236-Rev. P, 16-May-16						

DWG: 5347

Notes

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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